

**Fifth Semester B.E. Degree Examination, December 2012**  
**Fundamentals of CMOS VLSI**

Time: 3 hrs.

Max. Marks:100

**Note: Answer FIVE full questions, selecting  
at least TWO questions from each part.**

**PART - A**

- 1 a. Explain the nMOS fabrication process with neat diagram. (10 Marks)  
 b. Obtain the dc transfer characteristics of a CMOS inverter and mark all the region showing the status of PMOS and NMOS. (10 Marks)
- 2 a. Compare CMOS and bipolar technologies. (04 Marks)  
 b. Draw the circuit schematic and stick diagram of CMOS 2 input NAND gate. (06 Marks)  
 c. Draw the layout for the schematic shown in the Fig.Q.2(c). (10 Marks)

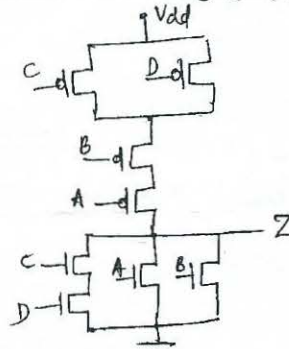


Fig.Q.2(c)

- 3 a. Explain the operation of CMOS dynamic logic. Also discuss the cascading problem of dynamic CMOS logic. (10 Marks)  
 b. Realize  $Z = \overline{A(B+C)} + DE$  for clocked CMOS logic. (05 Marks)  
 c. Find the equation for the node voltages  $V_1, V_2, V_3$  during logic "1" transfer, when each pass transistor is driving another pass transistor, as shown in Fig.Q.3(c). Assume threshold voltage of each transistor is  $V_{th}$ . (05 Marks)

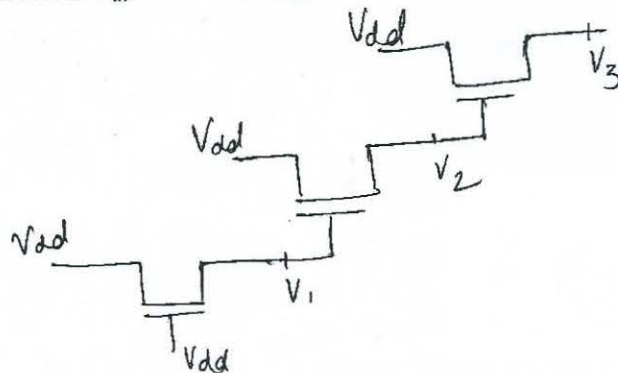


Fig.Q.3(c)

Important Note : 1. On completing your answers, compulsorily draw diagonal cross lines on the remaining blank pages.  
 2. Any revealing of identification, appeal to evaluator and /or equations written eg. 42+8 = 50, will be treated as malpractice.

- 4 a. Find the scaling factors for:  
i) Channel Resistance  $R_{on}$  (06 Marks)  
ii) Current density  $J$ . (08 Marks)  
b. Derive the equation for rise time and fall time for CMOS inverter. (08 Marks)  
c. Write a note on limitations of scaling. (06 Marks)

**PART – B**

- 5 a. Explain structured design of bus arbitration logic for n-line bus. (10 Marks)  
b. Explain dynamic 4-bit shift register using CMOS logic. (10 Marks)
- 6 a. Design 4-bit ALU to implement addition, subtraction, EXOR, EXNOR, OR and AND operations. (10 Marks)  
b. With the neat diagram, explain Braun array multiplier. (10 Marks)
- 7 a. Explain the working of three-transistor dynamic RAM cell. (06 Marks)  
b. Explain one transistor dynamic memory cell with schematic and stick diagram. (06 Marks)  
c. Discuss CMOS pseudo-static memory cell with stick diagram. (08 Marks)
- 8 a. Explain sensitized path-based testing for combinational logic. (10 Marks)  
b. Write a note on ground rules for successful design. (10 Marks)

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